

General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Features

cell density Trench technology
 $R_{DS(ON)}$ to minimize conductive loss

Product Summary

Application

nd Synchronous Rectifier

Ordering Information:

	TUBE
	1000

Absolute Maximum Ratings $T_C=25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C=25$	178	A
	$I_D @ T_C=75$	135	A
	$I_D @ T_C=100$	112	A
Pulsed Drain Current	I_{DM}	534	A
Total Power Dissipation	$P_D @ T_C=25$	113	W
Total Power Dissipation	$P_D @ T_A=25$	3.2	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	210	mJ

Fig.13 Resistive Switching Test Circuit

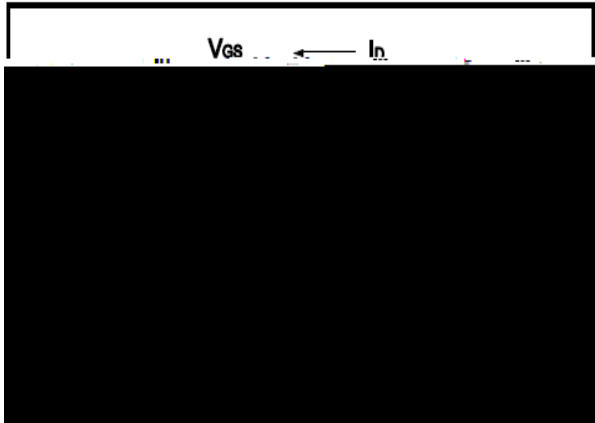


Fig.14 Resistive Switching Test Waveform

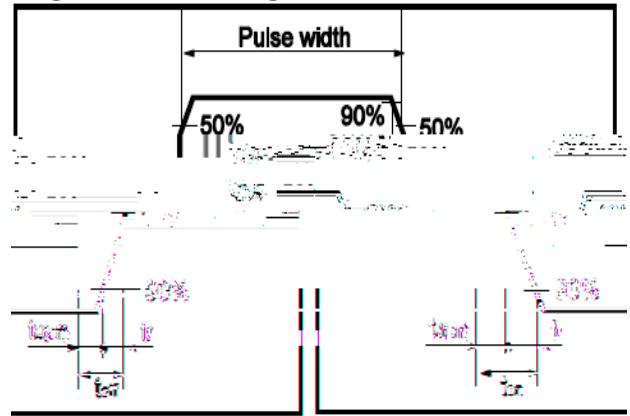


Fig.15 Avalanche Measurement Circuit

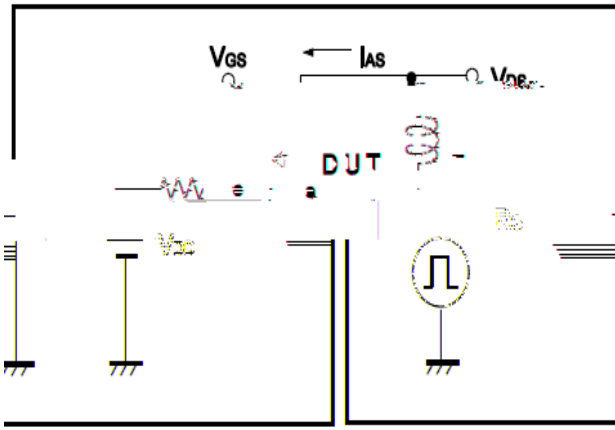
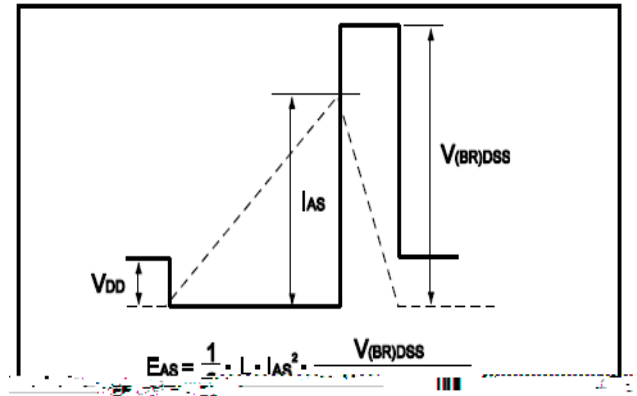


Fig.16 Avalanche Waveform





Dimensions (TO-220)

Unit mm

	2..		2 .				
	.		2.			0 2	.
	.		2.				2
	.		..		0 .		2 .
	. 1		.		1..	1 .	2..
	..		.		0 .		1..
	.		.		0..		1..
					1 .		1 .

